2019 19th International Workshop on Junction Technology (IWJT 2019)

Kyoto, Japan
6 – 7 June 2019

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Program/Contents

IWJT2019, Kyoto, Japan, June 6-7, 2019

June 6 (Thursday)

9:00 **Registration**
9:45 **Opening Remarks**

Keynote Speech

10:00 KN-1 **Reliability Considerations for the Qualification of Leading Edge CMOS Technologies**
[Keynote] Fernando Guarin / GLOBAL FOUNDRIES and IEEE EDS President ... 3

10:40 **Break** (10min)

Session 1 Junction Technology for Novel Devices (1)

10:50 S1-1 Withdrawn

11:20 S1-2 **Junction technology challenges and solutions for 3D device architecture**
[Invited] Yoshiaki Kikuchi / imec ... 6

11:50 S1-3 **Normally-Off Sputtered-MoS_2 nMISFETs with $MoSi_2$ Contact by Sulfur Powder Annealing and ALD Al_2O_3 Gate Dielectric for Chip Level Integration**
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